

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

15. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming an amorphous semiconductor film through a sputtering method over a plastic substrate;

adding a catalytic element into at least a portion of the semiconductor film, said catalytic element being capable of promoting crystallization; and

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

16. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming an amorphous semiconductor film comprising silicon and germanium through a sputtering method over a plastic substrate;

adding a catalytic element into at least a portion of the semiconductor film, said catalytic element being capable of promoting crystallization,

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

17. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming a base film on a plastic substrate;

forming a gate wiring on the base film;

forming a gate insulating film on the gate wiring;

forming an amorphous semiconductor film through a sputtering method on the gate insulating film;

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

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18. (Amended) A method for manufacturing a semiconductor device comprising a semiconductor circuit, said method comprising the steps of:

forming a gate wiring over a plastic substrate;

forming a gate insulating film on the gate wiring;

forming an amorphous semiconductor film through a sputtering method on the gate insulating film;

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crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

19. (Amended) A method for manufacturing an electroluminescence display device comprising at least a thin film transistor, said method comprising the steps of:

forming an amorphous semiconductor film through a sputtering method over a plastic substrate;

crystallizing the semiconductor film by irradiating with a laser light to form a crystalline semiconductor film;

forming a gate insulating film adjacent to the crystalline semiconductor film;

forming a gate electrode adjacent to the crystalline semiconductor film with the gate insulating film interposed therebetween;

introducing an impurity region into the crystalline semiconductor film to form at least a source region, a drain region and a channel region between the source and drain regions;

forming at least an interlayer insulating film over the thin film transistor;

forming a pixel electrode over the interlayer insulating film, said pixel electrode being electrically connected to the drain region of the thin film transistor;

forming an EL layer adjacent to the pixel electrode;

forming a cathode adjacent to the EL layer,

wherein an inert gas is used as a sputtering gas in the sputtering method, said inert gas being at least one gas selected from the group consisting of Ar, He, Ne and N.

Please add new claims 45 and 46 as follows.

--45. (New) A method according to claim 14, wherein the base film and the amorphous semiconductor film are formed in succession without exposure to the atmosphere.

46. (New) A method according to claim 17, wherein the base film and the amorphous semiconductor film are formed in succession without exposure to the atmosphere.--